

APM4463K



P-Channel Enhancement Mode MOSFET

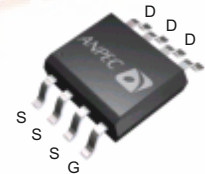
Features

- 20V/-10A ,
 $R_{DS(ON)} = 12m\Omega (typ.) @ V_{GS} = -4.5V$
 $R_{DS(ON)} = 18m\Omega (typ.) @ V_{GS} = -2.5V$
- Super High Dense Cell Design
- Reliable and Rugged
- SOP-8 Package
- Lead Free Available (RoHS Compliant)

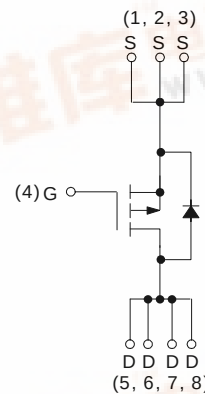
Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems

Pin Description



Top View of SOP – 8



P-Channel MOSFET

Ordering and Marking Information

APM4463 □□-□□□ Lead Free Code Handling Code Temp. Range Package Code	Package Code K : SOP-8 Operating Junction Temp. Range C : -55 to 150°C Handling Code TR : Tape & Reel Lead Free Code L : Lead Free Device Blank : Original Device
APM4463 K : APM4463 XXXXX	XXXXX - Date Code

Note: ANPEC lead-free products contain molding compounds/die attach materials and 100% matte in plate termination finish; which are fully compliant with RoHS and compatible with both SnPb and lead-free soldering operations. ANPEC lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J STD-020C for MSL classification at lead-free peak reflow temperature.

ANPEC reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Absolute Maximum Ratings $(T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Unit
V_{DSS}	Drain-Source Voltage	-20	V
V_{GSS}	Gate-Source Voltage	± 16	
I_D^*	Continuous Drain Current	$V_{GS} = -4.5\text{V}$	A
I_{DM}^*	Pulsed Drain Current		
I_S^*	Diode Continuous Forward Current	-2.3	A
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	
P_D^*	Maximum Power Dissipation	$T_A = 25^\circ\text{C}$	W
		$T_A = 100^\circ\text{C}$	
$R_{\theta JA}^*$	Thermal Resistance-Junction to Ambient	62.5	$^\circ\text{C/W}$

Note:

*Surface Mounted on 1in^2 pad area, $t \leq 10\text{sec}$.

Electrical Characteristics $(T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	APM4463K			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	-20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-16V, V _{GS} =0V			-1	μA
		T _J =85°C			-30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-0.7	-0.9	-1.5	V
I _{GSS}	Gate Leakage Current	V _{GS} =±16V, V _{DS} =0V			±100	nA
R _{DS(ON)} ^a	Drain-Source On-state Resistance	V _{GS} =-4.5V, I _{DS} =-10A		12	17	mΩ
		V _{GS} =-2.5V, I _{DS} =-8A		18	25	
V _{SD} ^a	Diode Forward Voltage	I _{SD} =-2.3A, V _{GS} =0V		-0.7	-1.3	V
Dynamic Characteristics ^b						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		5		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-15V, Frequency=1.0MHz		4540		pF
C _{oss}	Output Capacitance			1100		
C _{rss}	Reverse Transfer Capacitance			810		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-10V, R _L =10Ω, I _{DS} =-1A, V _{GEN} =-4.5V, R _G =6Ω		40	60	ns
T _r	Turn-on Rise Time			40	60	
t _{d(OFF)}	Turn-off Delay Time			170	270	
T _f	Turn-off Fall Time			90	150	

Electrical Characteristics (Cont.) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	APM4463K			Unit
			Min.	Typ.	Max.	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =-10V, V _{GS} =-4.5V, I _{DS} =-10A		37	45	nC
Q _{gs}	Gate-Source Charge			6.5		
Q _{gd}	Gate-Drain Charge			2.5		

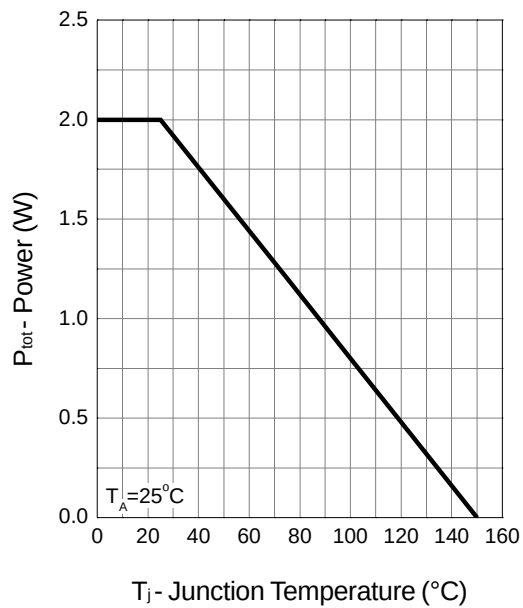
Notes:

a : Pulse test ; pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

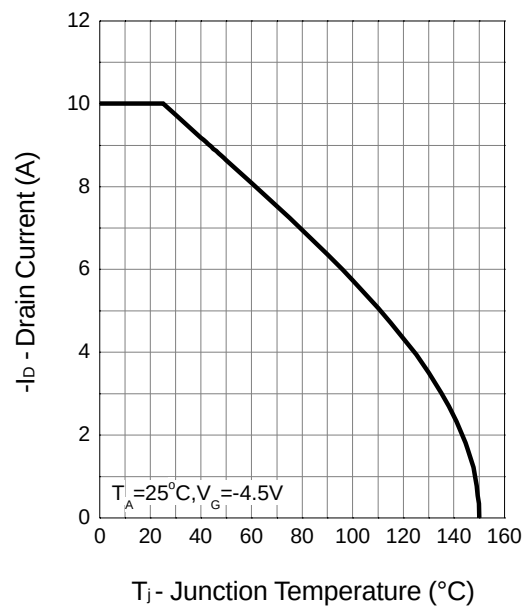
b : Guaranteed by design, not subject to production testing.

Typical Characteristics

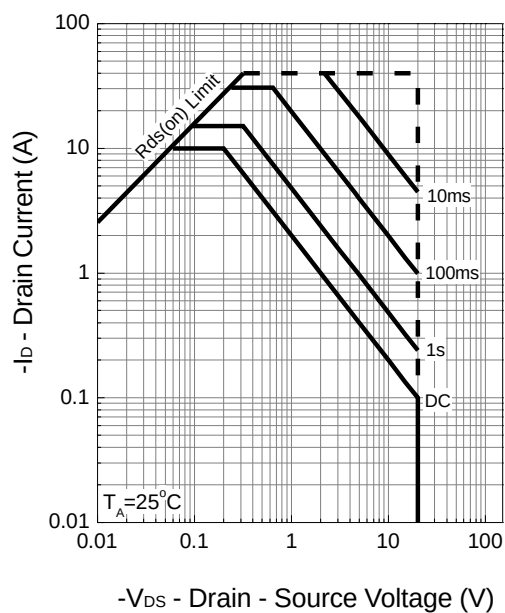
Power Dissipation



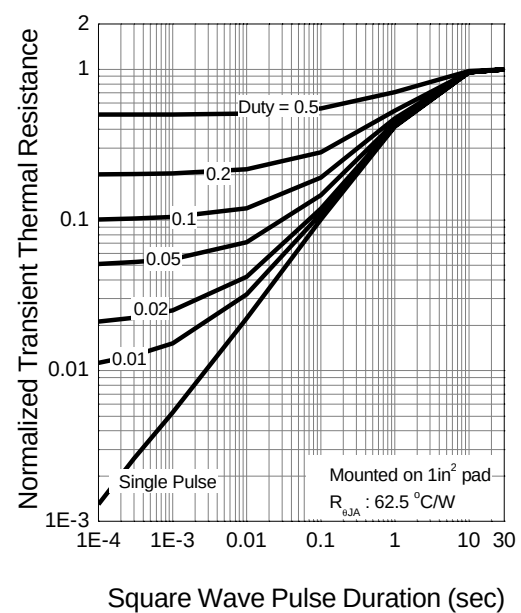
Drain Current



Safe Operation Area

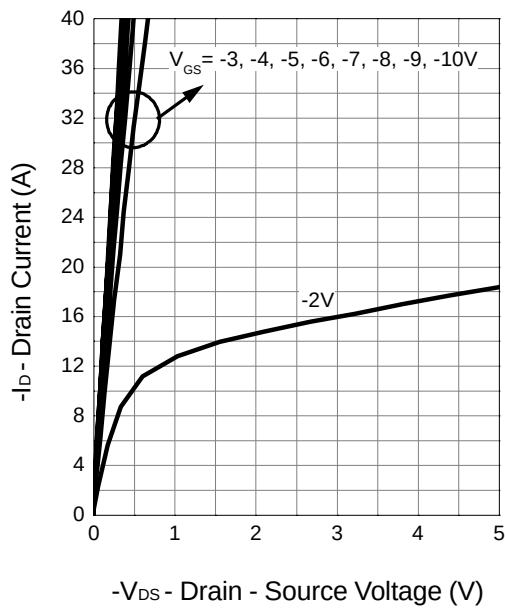


Thermal Transient Impedance

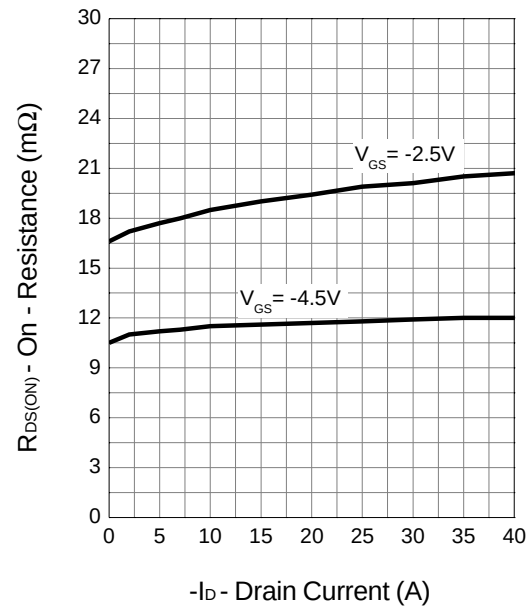


Typical Characteristics (Cont.)

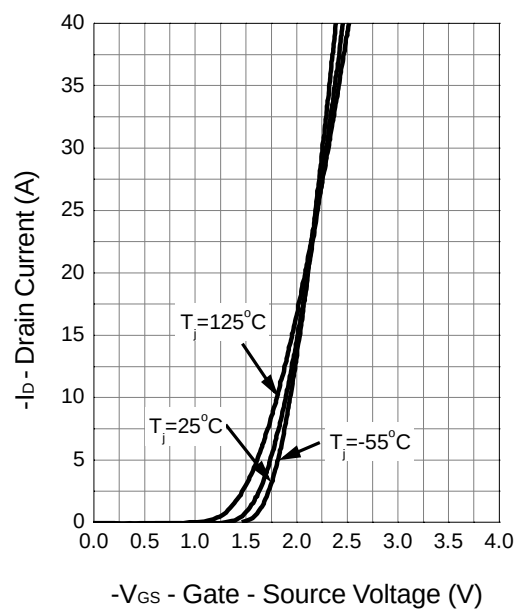
Output Characteristics



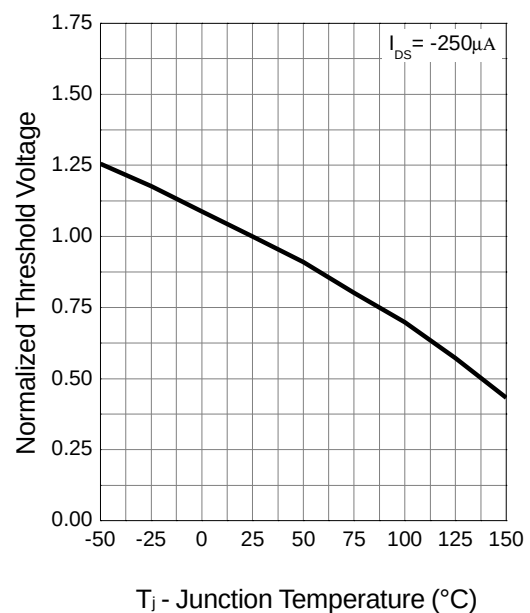
Drain-Source On Resistance



Transfer Characteristics

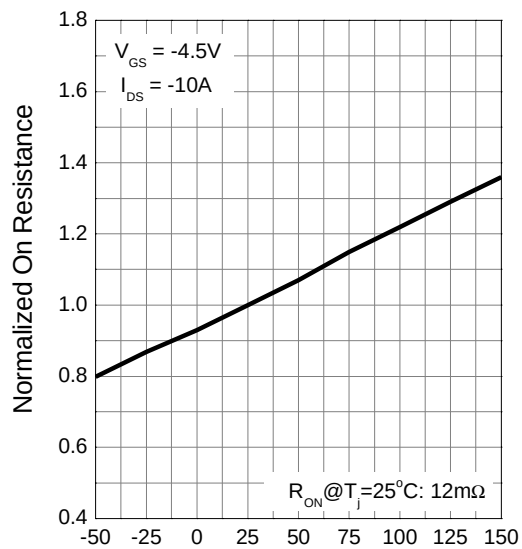


Gate Threshold Voltage



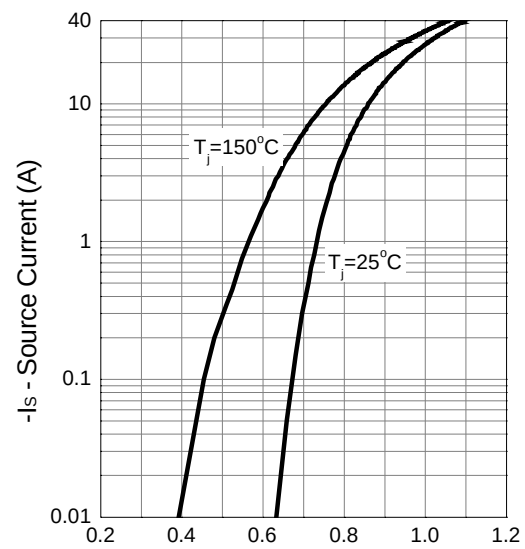
Typical Characteristics (Cont.)

Drain-Source On Resistance



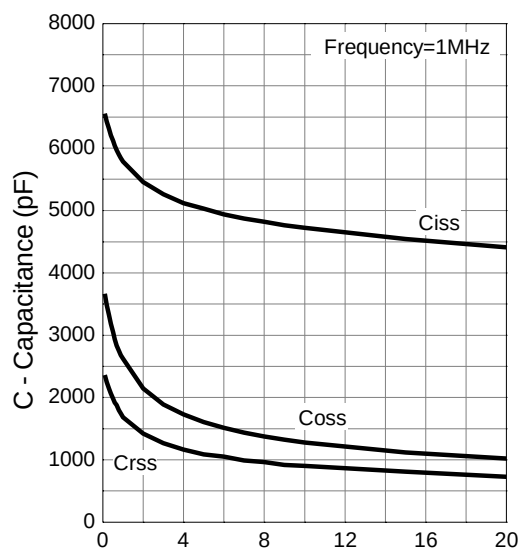
T_j - Junction Temperature ($^{\circ}\text{C}$)

Source-Drain Diode Forward



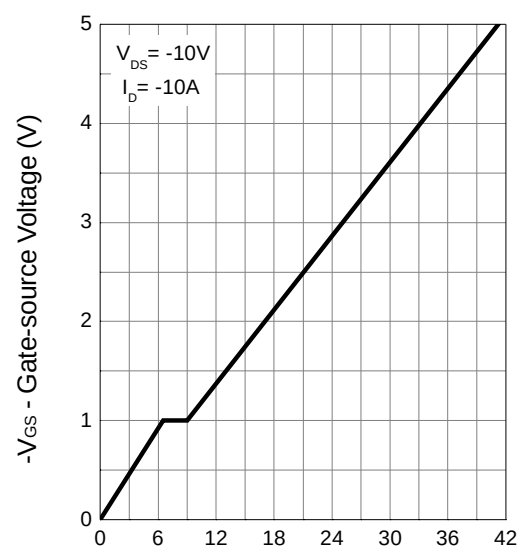
$-V_{SD}$ - Source - Drain Voltage (V)

Capacitance



$-V_{DS}$ - Drain - Source Voltage (V)

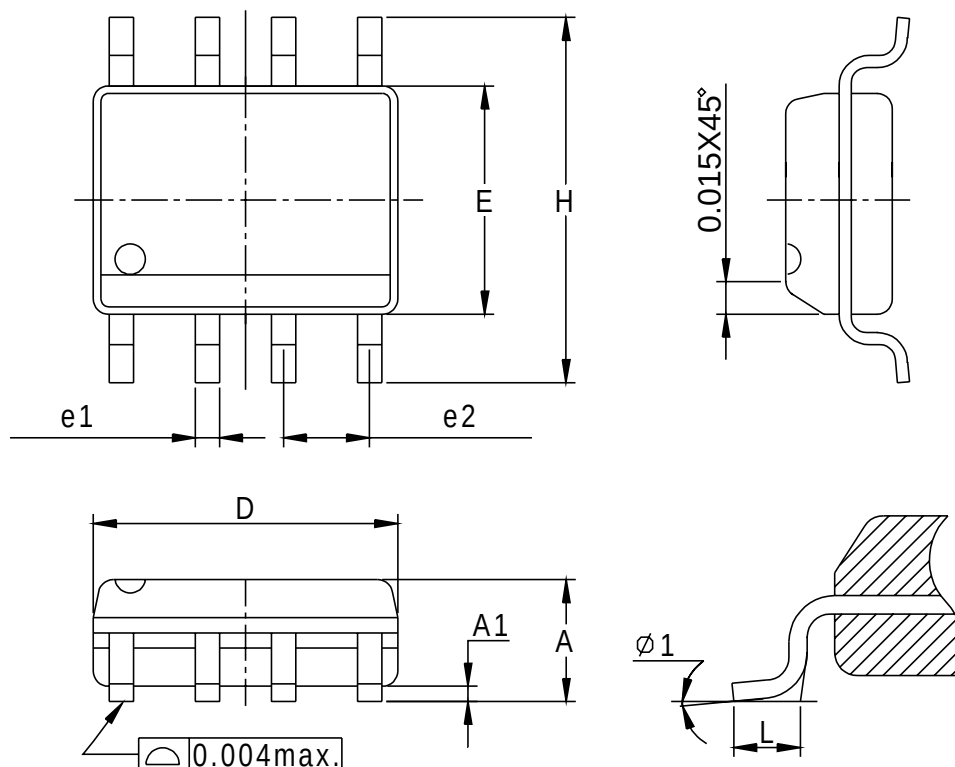
Gate Charge



Q_G - Gate Charge (nC)

Packaging Information

SOP-8 pin (Reference JEDEC Registration MS-012)



Dim	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
D	4.80	5.00	0.189	0.197
E	3.80	4.00	0.150	0.157
H	5.80	6.20	0.228	0.244
L	0.40	1.27	0.016	0.050
e1	0.33	0.51	0.013	0.020
e2	1.27BSC		0.50BSC	
Ø 1	8°		8°	

Classification Reflow Profiles(Cont.)

Table 1. SnPb Eutectic Process – Package Peak Reflow Temperatures

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	240 +0/-5°C	225 +0/-5°C
≥2.5 mm	225 +0/-5°C	225 +0/-5°C

Table 2. Pb-free Process – Package Classification Reflow Temperatures

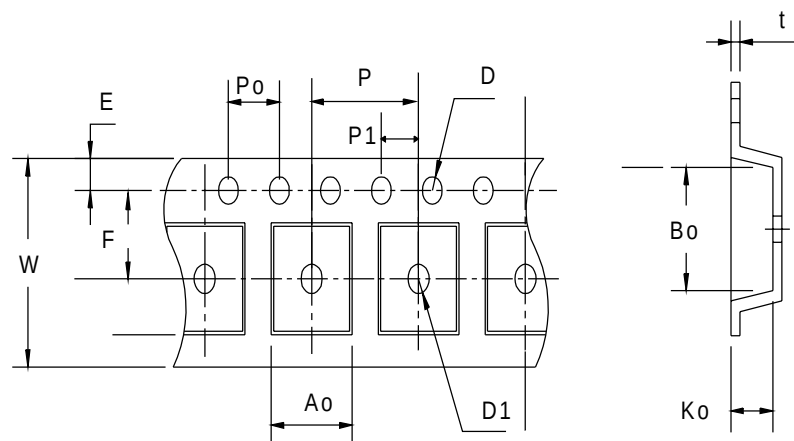
Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 +0°C*	260 +0°C*	260 +0°C*
1.6 mm – 2.5 mm	260 +0°C*	250 +0°C*	245 +0°C*
≥2.5 mm	250 +0°C*	245 +0°C*	245 +0°C*

*Tolerance: The device manufacturer/supplier **shall** assure process compatibility up to and including the stated classification temperature (this means Peak reflow temperature +0°C. For example 260°C+0°C) at the rated MSL level.

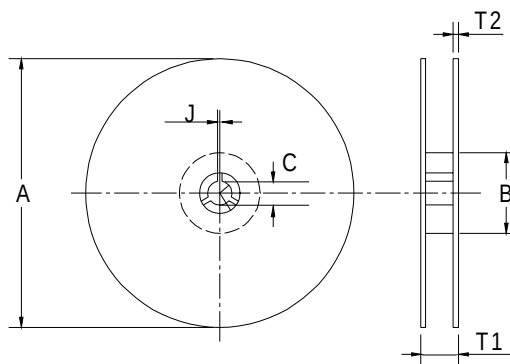
Reliability Test Program

Test item	Method	Description
SOLDERABILITY	MIL-STD-883D-2003	245°C, 5 SEC
HOLT	MIL-STD 883D-1005.7	1000 Hrs Bias @ 125°C
PCT	JESD-22-B, A102	168 Hrs, 100% RH, 121°C
TST	MIL-STD 883D-1011.9	-65°C ~ 150°C, 200 Cycles

Carrier Tape & Reel Dimensions



Carrier Tape & Reel Dimensions(Cont.)



Application	A	B	C	J	T1	T2	W	P	E
SOP-8	330±1	62 ± 1.5	12.75 + 0.15	2 + 0.5	12.4 +0.2	2± 0.2	12 + 0.3 - 0.1	8± 0.1	1.75± 0.1
	F	D	D1	Po	P1	Ao	Bo	Ko	t
	5.5 ± 0.1	1.55±0.1	1.55+ 0.25	4.0 ± 0.1	2.0 ± 0.1	6.4 ± 0.1	5.2± 0.1	2.1± 0.1	0.3±0.013

(mm)

Cover Tape Dimensions

Application	Carrier Width	Cover Tape Width	Devices Per Reel
SOP- 8	12	9.3	2500

Customer Service

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